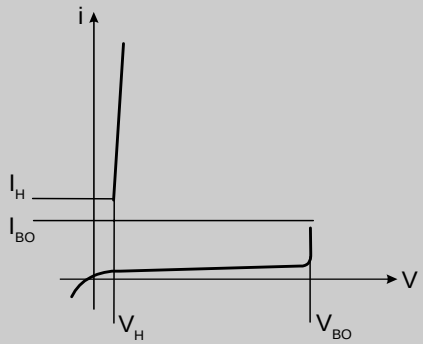
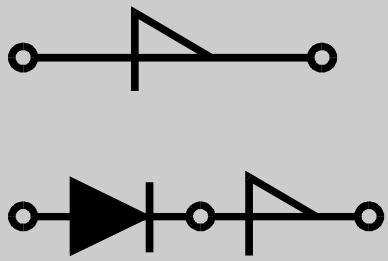
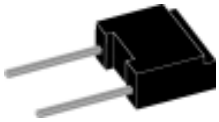
Applications

- Transient voltage protection
- High-voltage switches
- Crowbar
- Lasers
- Pulse generators





Application Note H - 6



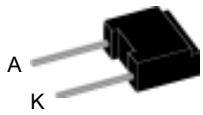
Remark: For special selection of more than 2 pieces IXBOD 1-... for every break down voltage of V_{BO} > 2000 V please contact us.

© 2000 IXYS All rights reserved

Single Breakover Diode

V_{BO} = 600-1000V
I_{AVM} = 0.9 A

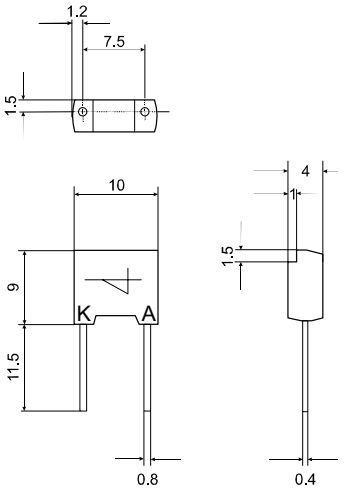
V_{BO} V	Standard Types
600 ±50	IXBOD 1 -06
700 ±50	IXBOD 1 -07
800 ±50	IXBOD 1 -08
900 ±50	IXBOD 1 -09
1000 ±50	IXBOD 1 -10



Symbol	Conditions	Ratings		
I_D	T_{VJ} = 125°C;	V = 0,8x V_{BO}	20	µA
V_{BO}			$V_{BO}(T_{VJ}) = V_{BO,\ 25°C}[1 + K_T(T_{VJ} - 25°C)]$	
I_{RMS}	f = 50 HZ;	T_{amb} = 50°C	1.4	A
	connection pins soldered to printed circuit (conductor 0,035x2mm)			
I_{AVM}			0.9	A
I_{SM}	t_p = 0.1 ms;	T_{amb} = 50°C non repetitive	200	A
I^2t	t_p = 0.1 ms;	T_{amb} = 50°C	2	A^2s
T_{amb}			-40...+125	°C
T_{stg}			-40...+125	°C
T_{VJm}			125	°C
K_T	Temperatur coefficient of V_{BO}		$2 \cdot 10^{-3}$	K^{-1}
K_P	coefficient for energy per pulse E_P (material constant)		700	K/Ws
R_{thJA}	- natural convection		60	K/W
	- with air speed 2 m/s		45	K/W
Weight			1	g

Symbol	Conditions		Characteristic Values	
I_{BO}	T_{VJ} = 25°C		15	mA
I_H	T_{VJ} = 25°C		30	mA
V_H	T_{VJ} = 25°C		4 - 8	V
$(dv/dt)_C$	T_{VJ} = 50°C;	$V_D = 0.67 \cdot (V_{BO} + 100V)$	> 1000	V/µs
$(di/dt)_C$	T_{VJ} = 125°C;	$V_D = V_{BO}$; I_T = 80A; f = 50 Hz	200	A/µs
$t_{q(typ)}$	T_{VJ} = 125°C	$V_D = 0.67 \cdot V_{BO}$; V_R = 0V	150	µs
	$dV/dt_{(lin.)}$ = 200V/µs; I_T = 80A; di/dt = -10A/µs			
V_T	T_{VJ} =125°C; I_T = 5A		1.7	V
$V_{(TO)}$	For power-loss calculations only		1.1	V
r_T	T_{VJ} = 125°C		0.12	Ω

Dimensions in mm (1 mm = 0.0394")



IXYS reserve at these the right to change limits, test conditions and dimensions; Data according to IEC 60747

030

© 2000 IXYS All rights reserved

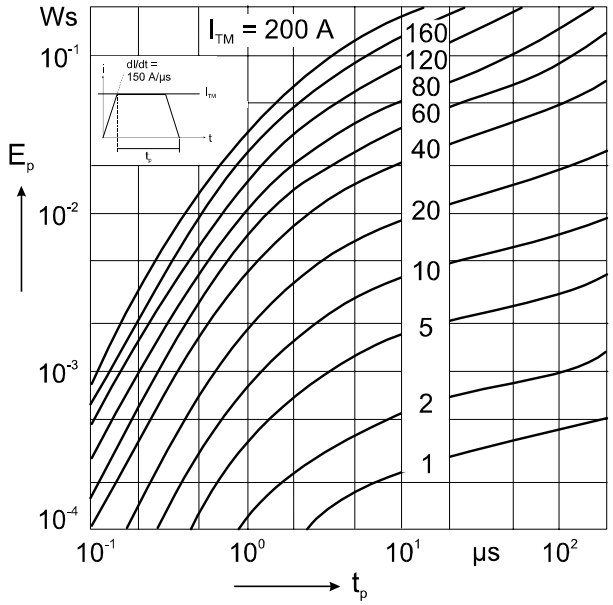


Fig. 1 Energy per pulse for trapezoidal current wafeforms (see waveform definition).

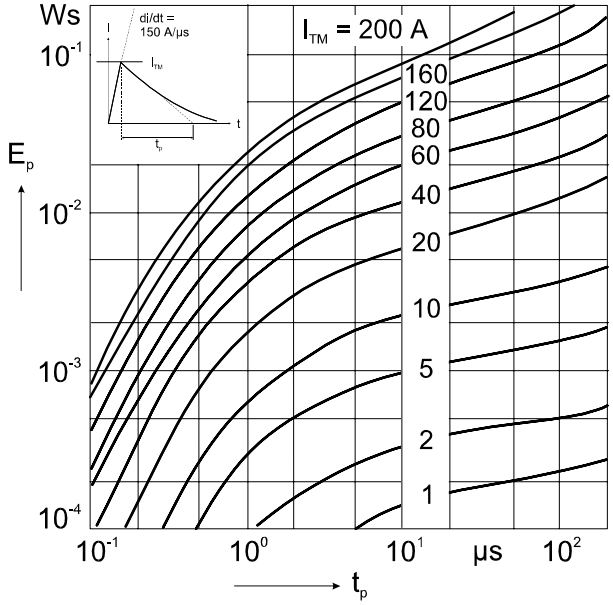


Fig. 2 Energy per pulse for exponentially decaying current pulse (see waveforms definition).

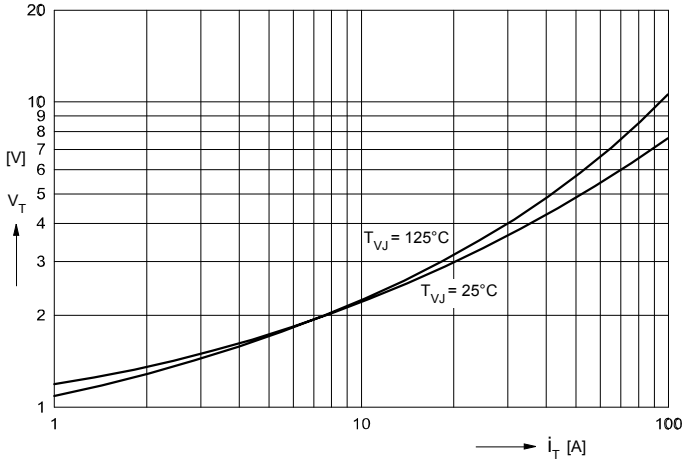


Fig. 3 On-state voltage

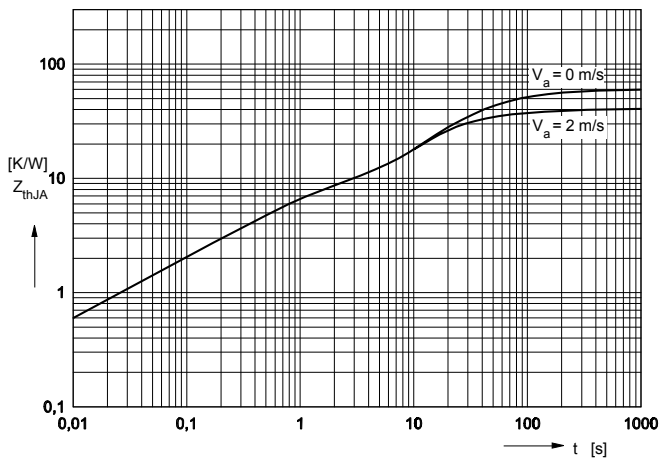
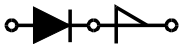


Fig. 4 Transient thermal resistance.

© 2000 IXYS All rights reserved

Breakover Diode Modules

Version: R Version: RD 

V_{BO} V	Standard Types	BOD - Elements	V_{BO} V	Standard Types	BOD - Elements	V_{BO} V	Standard Types	BOD - Elements
1200 ±50	IXBOD 1 -12R(D)	2	2000 ±50	IXBOD 1 -20R(D)	3	3400 ±100	IXBOD 1 -34R	4
1300 ±50	IXBOD 1 -13R(D)	2	2100 ±50	IXBOD 1 -21R(D)	3	3600 ±100	IXBOD 1 -36R	4
1400 ±50	IXBOD 1 -14R(D)	2	2200 ±50	IXBOD 1 -22R(D)	3	3800 ±100	IXBOD 1 -38R	4
1500 ±50	IXBOD 1 -15R(D)	2	2300 ±50	IXBOD 1 -23R(D)	3	4000 ±100	IXBOD 1 -40R	4
1600 ±50	IXBOD 1 -16R(D)	2	2400 ±50	IXBOD 1 -24R(D)	3	4200 ±100	IXBOD 1 -42R	4
1700 ±50	IXBOD 1 -17R(D)	2	2500 ±50	IXBOD 1 -25R(D)	3			
1800 ±50	IXBOD 1 -18R(D)	2	2600 ±100	IXBOD 1 -26R(D)	3			
1900 ±50	IXBOD 1 -19R(D)	2	2800 ±100	IXBOD 1 -28R(D)	3			
			3000 ±100	IXBOD 1 -30R(D)	3			
			3200 ±100	IXBOD 1 -32R(D)	3			

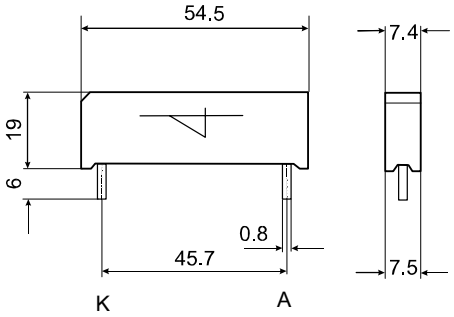
Symbol	Test Conditions	2 BODs	3 BODs	4 BODs	2-3 BODs D-Version	
I_D	T_{VJ} = 125°C; V = 0,8x V_{BO}	100	100	100	100	µA
V_{BO}					$V_{BO}(T_{VJ}) = V_{BO,\ 25°C}\,[1 + K_T\,(T_{VJ} - 25°C)]$	
I_{RMS}	f = 50 HZ; T_{amb} = 50°C connection pins soldered to printed circuit (conductor 0,035x2mm)	2.0	1.4	1.1	0.3	A
I_{AVM}		1.25	0.9	0.7	0.2	A
I_{SM}	t_p = 0.1 ms; T_{amb} = 50°C non repetitive	200	200	200	50	A
I^2t	t_p = 0.1 ms; T_{amb} = 50°C	2	2	2	0.125	A^2s
V_T	T_{VJ} =125°C; I_T = 5A	3.4	5.1	6.8	27	V
$V_{(TO)}$	For power-loss calculations only	2.2	3.3	4.4	17.5	V
r_T	T_{VJ} =125°C	0.24	0.36	0.48	3	Ω
T_{amb}		-40...+125	-40...+125	-40...+125	-40...+125	°C
T_{stg}		-40...+125	-40...+125	-40...+125	-40...+125	°C
T_{VJm}		125	125	125	125	°C
K_T	Temperatur coefficient of V_{BO}	$2{\cdot}10^{-3}$	$2{\cdot}10^{-3}$	$2{\cdot}10^{-3}$	$2{\cdot}10^{-3}$	K^{-1}
K_P	coefficient for energy per pulse E_P (material constant)	700	700	700	700	K/Ws
R_{thJA}	- natural convection	20	20	20	20	K/W
	- with air speed 2 m/s	16	16	16	16	K/W
Weight	typical	14	14	14	14	g

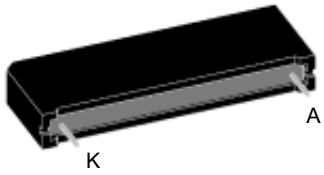
Symbol	Test Conditions Characteristic Values both Versions R & RD	2 BODs	3 BODs	4 BODs	
I_{BO}	T_{VJ} = 25°C	15	15	15	mA
I_H	T_{VJ} = 25°C	30	30	30	mA
V_H	T_{VJ} = 25°C	4 - 8	4 - 8	4 - 8	V
$(dv/dt)_C$	T_{VJ} = 50°C; $V_D = 0.67{\cdot}(V_{BO} + 100V)$				
	- V_{BO} bis 1500V	> 1000	-	-	V/µs
	- V_{BO} 1600 - 2000V	> 1500	-	-	V/µs
	- V_{BO} 2100 - 2500V	-	> 2000	-	V/µs
	- V_{BO} 2600 - 3000V	-	> 2500	-	V/µs
	- V_{BO} 3200 - 3400V	-	-	> 3000	V/µs
	- V_{BO} 3600 - 4200V	-	-	> 3500	V/µs
$(di/dt)_C$	T_{VJ} = 125°C; $V_D = V_{BO}$; I_T = 80A; f = 50 Hz	200	200	200	A/µs
$t_{q(typ)}$	T_{VJ} = 125°C $V_D = 0.67{\cdot}V_{BO}$; V_R = 0V $dv/dt_{(lin.)}$ = 200V/µs; I_T = 80A; di/dt = -10A/µs	150	150	150	µs

IXYS reserve at these the right to change limits, test conditions and dimensions; Data according to IEC 60747

032

© 2000 IXYS All rights reserved





Dimensions in mm (1 mm = 0.0394")

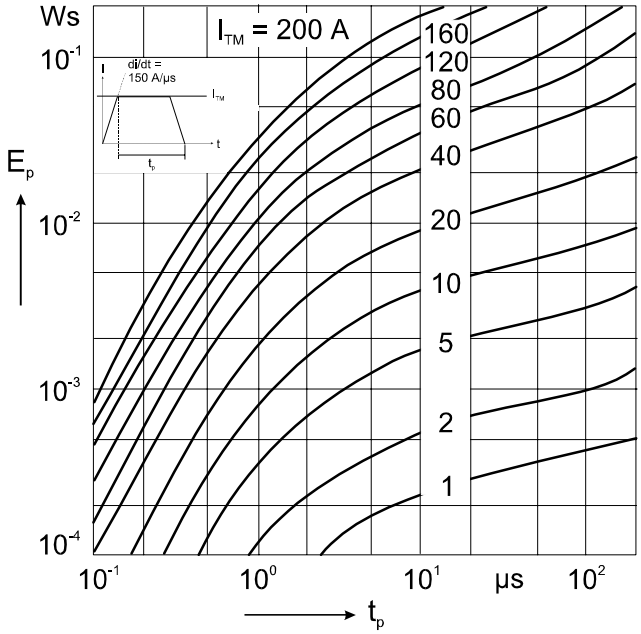


Fig. 5 Energy per pulse for single BOD element for trapezoidal wave current. E_P must be multiplied by number of elements for total energy.

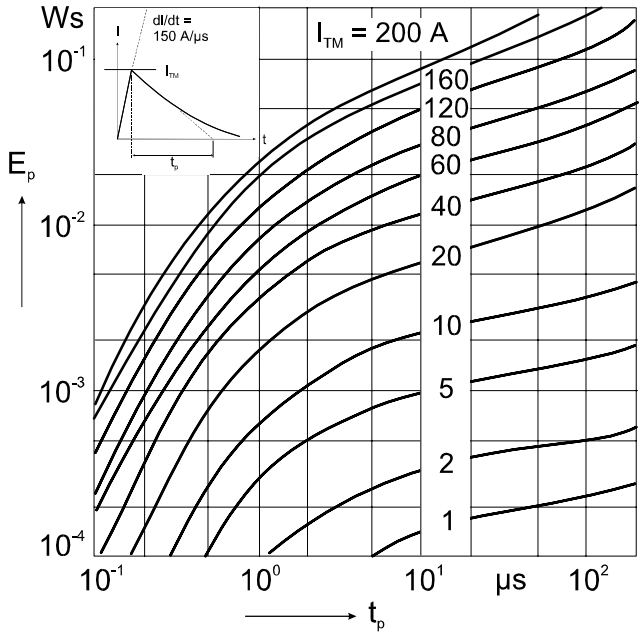


Fig. 6 Energy per pulse for single BOD element for exponentially decaying current pulse. E_P must be multiplied by number of elements for total energy.

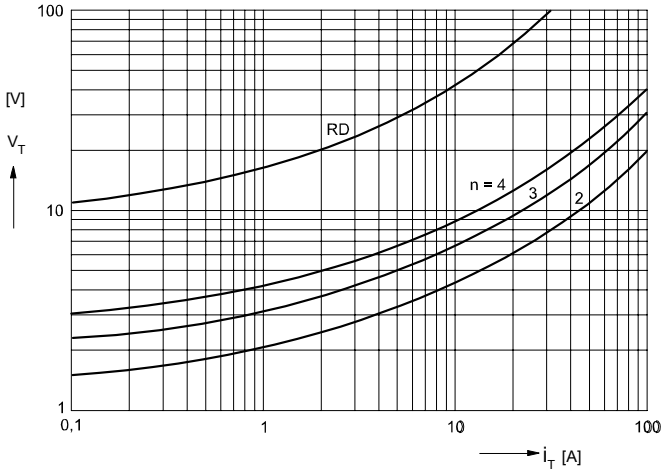


Fig. 7 On-state voltage at T_{VJ} = 125°C.

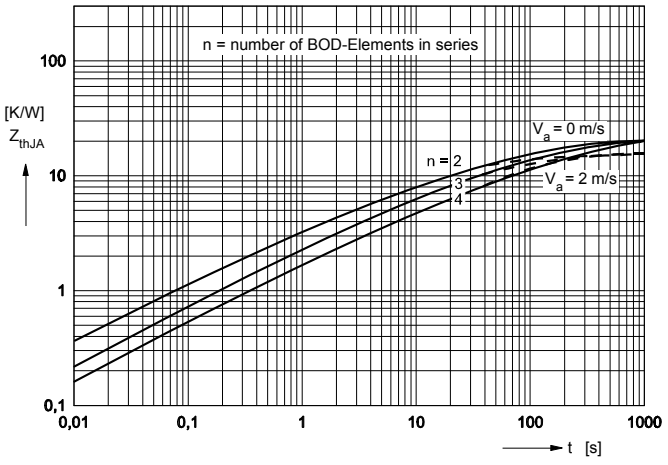


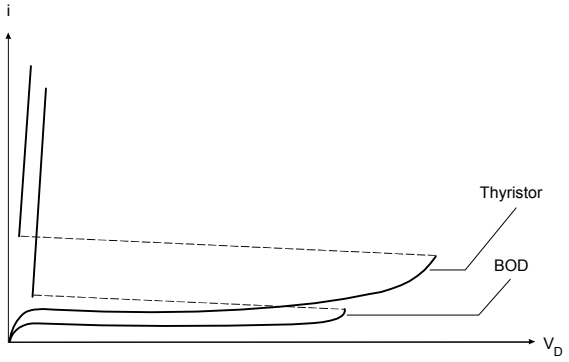
Fig. 8 Transient thermal resistance.

© 2000 IXYS All rights reserved

Application

Protection of thyristors against overvoltages in forward direction.

$$V_{BO}\ (T_{VJ}) = V_{BO,\ 25°C}\ [1+KT(T_{VJ} - 25°C)]$$



Calculation example

a. The maximum junction temperature shall be calculated for a module IXBOD 1 -30R at an ambient temperature T_a = 60 °C, an exponentially decaying current I_{TM} = 40A, a pulsewidth tp = 2 µs, an operating frequency f = 50 Hz and natural convection. From the diagram Fig. 6 the energy per pulse is obtained:

$$E_{p1} = 6 \times 10^{-3}\ Ws$$

For a module IXBOD1-30R the number of single IXBOD elements is:

$$n = 3$$

At natural air cooling the thermal resistance junction to ambient amounts to (Fig.8):

$$R_{thJA} = 20K/W$$

and the unknown temperature can be calculated as:

$$T_{VJmax1} = T_a + n \bullet f \bullet E_p \bullet R_{thJA} + K_p \bullet E_p$$

$$T_{VJmax1} = 60 + 18 + 4.2 = 82.2°C$$

b. If following these steady-state conditions an overload for 1 minute occurs with I_{TM}= 60 A and a pulse-width tp = 4 µs at the same operating frequency f = 50 Hz, then the resulting maximum junction temperature is calculating as follows:

$$T_{VJmax2} = T_{VJmax1} + (E_{p2}-E_{p1}) \bullet n \bullet f \bullet Z_{thJA}(t) + Kp \bullet (E_{p2}-E_{p1})$$

The diagrams Fig. 11 and Fig. 8 show

$$E_{p2} = 14 \times 10^{-3}\ Ws$$
$$Z_{thJA}(t = 1min) = 12K/W$$

From what follows:

$$T_{VJmax2} = 82.2 + 14.4 + 5,6 = 102.2\ °C$$

which is allowed because the maximum admissible junction temperature T_{VJM} = 125 °C.

© 2000 IXYS All rights reserved

Example of a circuit

A simple emergency triggering circuit.

T : Thyristor

R_1 : Current limiting resistance (0 - 200 Ω)

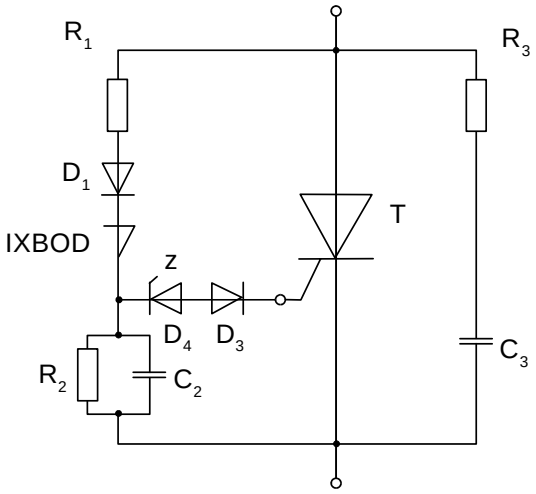
D_1 : Series-diode (fast recovery diode)

D_3 : Protection diode

D_4 : Zener diode, typical V_Z: 3-6 V

R_2, C_2 : Protection against parasitic triggering; recommended values:
R_2 : 100 - 1000 Ω
C_2 : 22 - 47 nF

R_3, C_3 : Snubber network of the thyristor



Notice

1. A IXBOD element has a maximum reverse blocking voltage of 10V.

2. For higher reverse voltages a fast, soft recovery diode must be connected in series (Fig. 9). This diode must fulfill the conditions of Fig. 10.

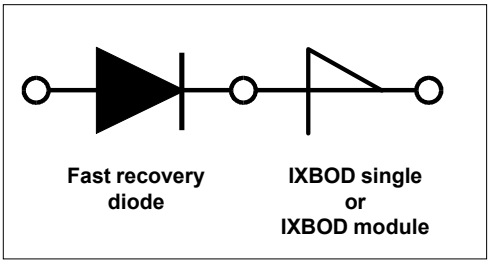


Fig. 9 IXBOD protection by a fast recovery diode.

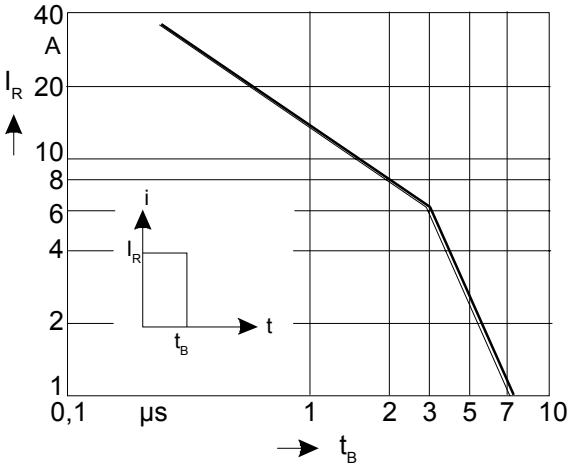


Fig. 10 Maximum peak value of the reverse current admissible for a given pulse-width t_B, which is required for the suitable fast recovery series-diode.

© 2000 IXYS All rights reserved

© 2000 IXYS All rights reserved

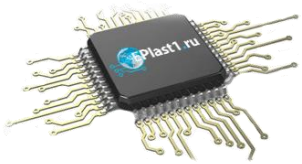
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.